

L15 ANSWER 9 OF 12 HCPLUS COPYRIGHT 2003 ACS on STN  
 AN 1999:796011 HCPLUS  
 DN 132:43780  
 TI Formation of dielectric layers  
 IN Narwankar, Pravin K.; Sahin, Turgut; Urdahl, Randall S.; Velaga, Ankineedu; Liu, Patricia  
 PA Applied Materials, Inc., USA  
 SO PCT Int. Appl., 41 pp.  
 CODEN: PIXXD2  
 DT Patent  
 LA English  
 IC ICM C23C016-56  
 ICS C23C016-40; H01L021-3105  
 CC 76-10 (Electric Phenomena)  
 Section cross-reference(s): 75

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI WO 9964645 A1 19991216 WO 1999-US13300 19990611  
 W: JP, KR  
 RW: AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL,  
 PT, SE  
 US 2002009861 A1 20020124 US 1998-96858 19980612  
 EP 1093532 A1 20010425 EP 1999-930223 19990611  
 R: BE, DE, GB, NL, IE  
 JP 2002517914 T2 20020618 JP 2000-553633 19990611  
 PRAI US 1998-96858 A 19980612  
 WO 1999-US13300 W 19990611  
 AB An active at. species is generated in a 1st chamber. A dielec. layer formed on a substrate is then exposed to the active at. species in a 2nd chamber sep. from the 1st chamber.  
 IT 6074-84-6, Pentaethoxytantalum 172901-22-3  
 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)  
 (in formation of dielec. layers)  
 RN 6074-84-6 HCPLUS  
 CN Ethanol, tantalum(5+) salt (9CI) (CA INDEX NAME)

H<sub>3</sub>C—CH<sub>2</sub>—OH

1/5 Ta(V)

RN 172901-22-3 HCPLUS  
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)

